NPN Epitaxial Planar Silicon Transistor



2SC3808

# High hfe, Low-Frequency General-Purpose Amplifier Applications

## **Applications**

· Low frequency general-purpose amplifiers, drivers.

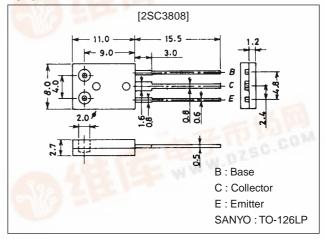
## **Features**

- · Large current capacity (I<sub>C</sub>=2A).
- · Adoption of MBIT process.
- · High DC current gain (h<sub>FE</sub>=800 to 3200)
- · Low collector-to-emitter saturation voltage  $(V_{CE(sat)} \le 0.5V)$ .
- · High V<sub>EBO</sub> (V<sub>EBO</sub>≥15V).

## **Package Dimensions**

unit:mm

#### 2043A



## **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CBO</sub>		80	V
Collector-to-Emitter Voltage	V <sub>CEO</sub>		60	V
Emitter-to-Base Voltage	V <sub>EBO</sub>	100	15	V
Collector Current	lc	The same of the sa	2	Α
Collector Current (Pulse)	ICP	- LA [17]	4	Α
Collector Dissipation	PC	AND AND LESS W	1.2	W
		Tc=25°C	15	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg	D and	-55 to +150	°C

### Electrical Characteristics at Ta = 25°C

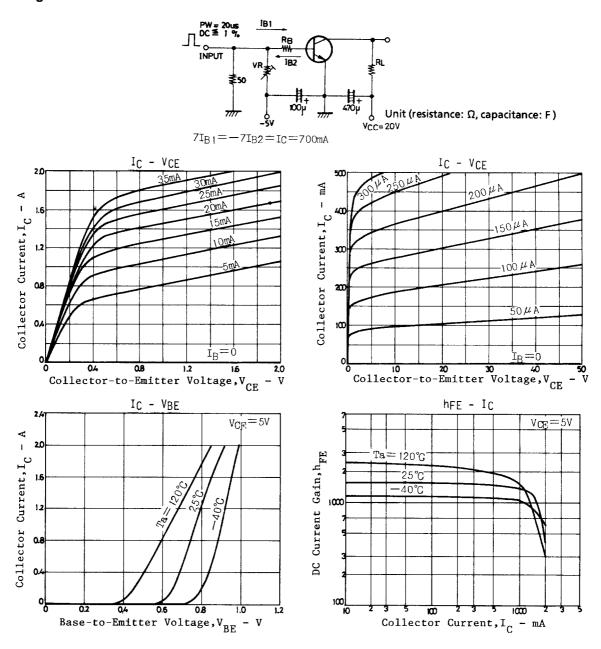
Parameter	Symbol	Conditions	Ratings			Unit
	Symbol		min	typ	max	Offic
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =50V, I <sub>E</sub> =0			1	μΑ
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =10V, I <sub>C</sub> =0			1	μΑ
DC Current Gain	h <sub>FE</sub> 1	V <sub>CE</sub> =5V, I <sub>C</sub> =500mA	800	1500	3200	
	h <sub>FE</sub> 2	V <sub>CE</sub> =5V, I <sub>C</sub> =1A	600	MI.D.		
Gain-Bandwidth Product	fT	V <sub>CE</sub> =10V, I <sub>C</sub> =50mA		170		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, f=1MHz		24		pF

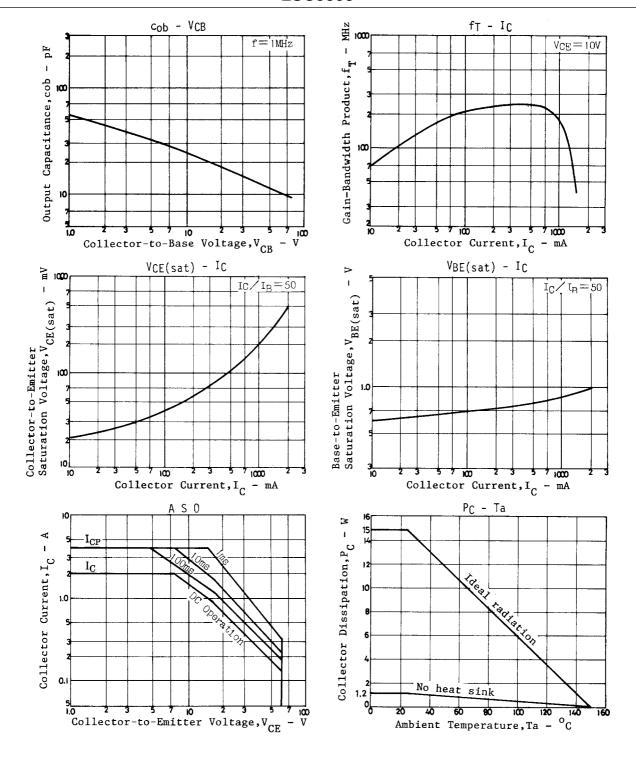
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	O III
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =1A, I <sub>B</sub> =20mA		0.2	0.5	V
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =1A, I <sub>B</sub> =20mA		0.87	1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =10μA, I <sub>E</sub> =0	80			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =1mA, R <sub>BE</sub> =∞	60			V
Emitter-to-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =10μA, I <sub>C</sub> =0	15			V
Turn-ON Time	ton	See specified test circuit.		0.23		μs
Storage Time	t <sub>stg</sub>	See specified test circuit.		2.7		μs
Fall Time	t <sub>f</sub>	See specified test circuit.		0.75		μs

## **Switching Time Test Circuit**





#### 2SC3808

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